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FDY301NZ

Single N-Channel 2.5V Specified PowerTrench® MOSFET

General Description

This Single N-Channel MOSFET has been designed using Fairchild Semiconductor's advanced Power Trench process to optimize the $R_{\text{DS(ON)}} \textcircled{Q} \ V_{\text{GS}} = 2.5 \text{v}.$

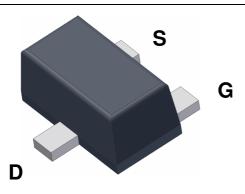
Applications

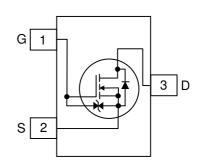
Li-Ion Battery Pack



Features

- 200 mA, 20 V $R_{DS(ON)} = 5~\Omega$ @ $V_{GS} = 4.5~V$ $R_{DS(ON)} = 7~\Omega$ @ $V_{GS} = 2.5~V$
- ESD protection diode (note 3)
- RoHS Compliant





Absolute Maximum Ratings T_A=25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DSS}	Drain-Source Voltage	20	V
V_{GSS}	Gate-Source Voltage	± 12	٧
I _D	Drain Current - Continuous (Note 1a	(a) 200	mA
	– Pulsed	1000	
P_D	Power Dissipation (Steady State) (Note 1a	ta) 625	mW
	(Note 1b	1 446	
T_J , T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	°C

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1a)	1a) 200	°C/W
R _{eJA}	Thermal Resistance, Junction-to-Ambient (Note 1b)	280	

Package Marking and Ordering Information

	<u> </u>	<u> </u>		
Device Marking	Device	Reel Size	Tape width	Quantity
D	FDY301NZ	7"	8 mm	3000units

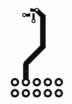
Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Char	acteristics			1	l u	
BV _{DSS}	Drain–Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, \qquad I_D = 250 \mu\text{A}$	20			V
ΔBV _{DSS} ΔT _J	Breakdown Voltage Temperature Coefficient	I_D = 250 μ A, Referenced to 25°C		14		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 16 \text{ V}, \qquad V_{GS} = 0 \text{ V}$			1	μΑ
I_{GSS}	Gate-Body Leakage,	$V_{GS} = \pm 12 \text{ V}, V_{DS} = 0 \text{ V}$			± 10	μΑ
		$V_{GS} = \pm 4.5 \text{ V}, V_{DS} = 0 \text{ V}$			± 1	μA
On Char	acteristics (Note 2)					
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	0.6	-	1.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	I_D = 250 μ A, Referenced to 25 $$ C		2.8		mV/°C
$R_{DS(on)}$	Static Drain–Source On–Resistance	$\begin{array}{llllllllllllllllllllllllllllllllllll$			5 7 9 10 7	Ω
g _{FS}	Forward Transconductance	$V_{DS} = 5 \text{ V}, \qquad I_{D} = 200 \text{ mA}$		1.1		S
Dvnamic	Characteristics					
C _{iss}	Input Capacitance	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V},$		60		pF
Coss	Output Capacitance	f = 1.0 MHz		20		pF
C _{rss}	Reverse Transfer Capacitance			10		pF
Switchin	g Characteristics (Note 2)					
t _{d(on)}	Turn-On Delay Time	$V_{DD} = 10 \text{ V}, \qquad I_D = 1 \text{ A},$		6	12	ns
t _r	Turn-On Rise Time	$V_{GS} = 4.5 \text{ V}, \qquad R_{GEN} = 6 \Omega$		8	16	ns
t _{d(off)}	Turn-Off Delay Time			8	16	ns
t _f	Turn-Off Fall Time			2.4	4.8	ns
Q _g	Total Gate Charge	$V_{DS} = 10 \text{ V}, \qquad I_{D} = 200 \text{ mA},$		0.8	1.1	nC
Q _{gs}	Gate-Source Charge	$V_{GS} = 4.5 \text{ V}$		0.16		nC
Q_{gd}	Gate-Drain Charge			0.26		nC
Drain-So	ource Diode Characteristics	and Maximum Ratings				
V _{SD}	Drain–Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_{S} = 150 \text{ mA} \text{ (Note 2)}$		0.7	1.2	V
t _{rr}	Diode Reverse Recovery Time	I _F = 200 mA,		12		nS
Qrr	Diode Reverse Recovery Charge	$dI_F/dt = 100 A/\mu s$		3		nC

Notes:

1. R_{eJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{eJC} is guaranteed by design while R_{eCA} is determined by the user's board design.



a) 200 °C/W when mounted on a 1in² pad of 2 oz copper



- b) 280 °C/W when mounted on a minimum pad of 2 oz copper Scale 1 : 1 on letter size paper
- 2. Pulse Test: Pulse Width < 300 μ s, Duty Cycle < 2.0%
- The diode connected between the gate and source serves only as protection againts ESD. No gate overvoltage rating is implied.

Typical Characteristics

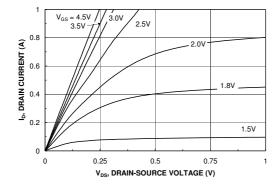


Figure 1. On-Region Characteristics.

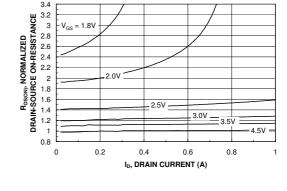


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

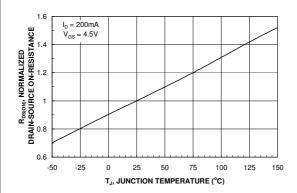


Figure 3. On-Resistance Variation with Temperature.

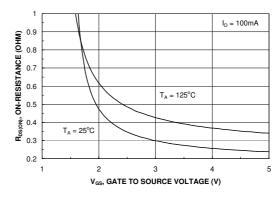


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

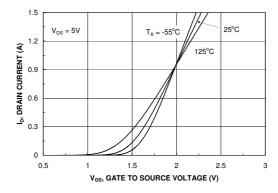


Figure 5. Transfer Characteristics.

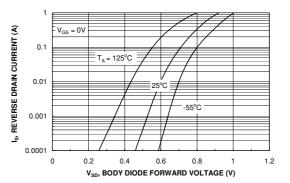
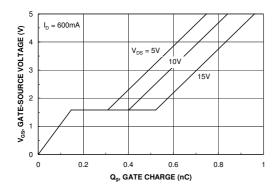


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics



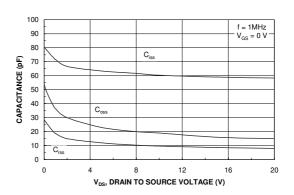
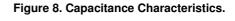
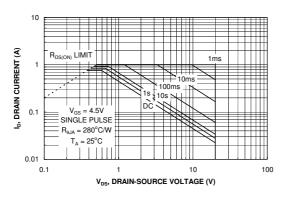


Figure 7. Gate Charge Characteristics.





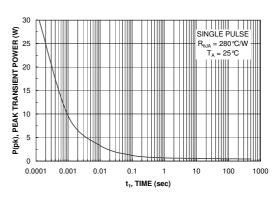


Figure 9. Maximum Safe Operating Area.

Figure 10. Single Pulse Maximum Power Dissipation.

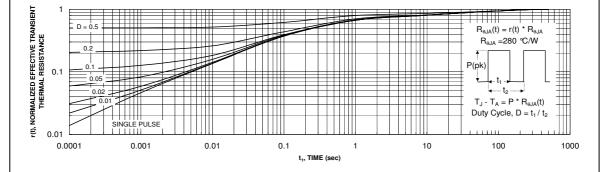
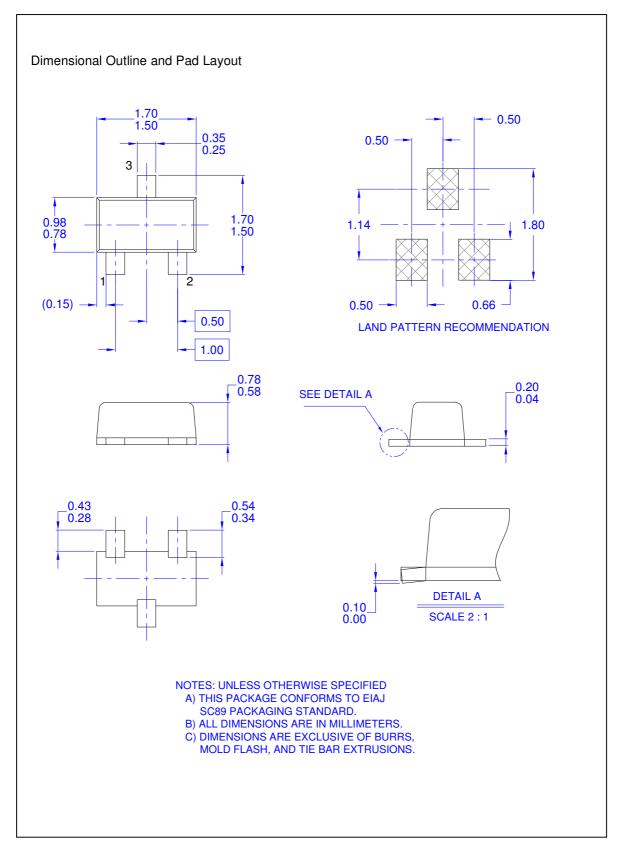


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1b. Transient thermal response will change depending on the circuit board design.



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